

Modeling of Multilayer Ion Etching Processes

E. Barouch, S.A. Orszag
Program in Applied and Computational Mathematics,
Princeton University, Princeton, NJ, 08540, USA

S.J. Sherwin, G.E. Karniadakis
Department of Mechanical and Aerospace Engineering,
Princeton University, Princeton, NJ, 08540, USA

Submitted to JVSTB for Rapid Communication, March 26, 1993.

ABSTRACT

Numerical simulation is used to model ion etching in tri-layer lithography. The simulations are capable of capturing the evolution of the boundary between two materials as well as the physically observed phenomena *RIE lag* and undercutting. Numerical results are compared with experimental data and a good agreement is found except close to the material interface where the slope of the surface is large. This error is attributed to a purely energy dependent yield used in the simulations.